



AO4435

P-Channel Enhancement Mode Field Effect Transistor



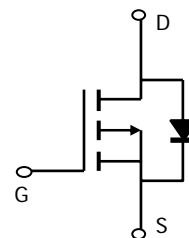
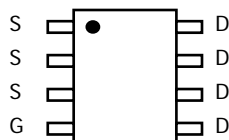
General Description

The AO4435 uses advanced trench technology to provide excellent $R_{DS(ON)}$, and ultra-low low gate charge with a 25V gate rating. This device is suitable for use as a load switch or in PWM applications. Standard Product AO4435 is Pb-free (meets ROHS & Sony 259 specifications).

Features

$V_{DS} = -30V$
 $I_D = -10A$ ($V_{GS} = -10V$)
 $R_{DS(ON)} < 18m\Omega$ ($V_{GS} = -10V$)
 $R_{DS(ON)} < 36m\Omega$ ($V_{GS} = -5V$)

SOIC-8
Top View



Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	10 Sec	Steady State	Units	
Drain-Source Voltage	V_{DS}	-30		V	
Gate-Source Voltage	V_{GS}	±25		V	
Continuous Drain Current ^A	I_D	$T_A=25^\circ C$	-10	-8	A
		$T_A=70^\circ C$	-8	-6	
Pulsed Drain Current ^B	I_{DM}	-80			
Power Dissipation ^A	P_D	$T_A=25^\circ C$	3.1	1.7	W
		$T_A=70^\circ C$	2.0	1.1	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150		°C	

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A $t \leq 10s$	$R_{\theta JA}$	32	40	°C/W
Maximum Junction-to-Ambient ^A Steady State		60	75	°C/W
Maximum Junction-to-Lead ^C Steady State	$R_{\theta JL}$	17	24	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D = -250\mu\text{A}, V_{GS} = 0\text{V}$	-30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -30\text{V}, V_{GS} = 0\text{V}$ $T_J = 55^\circ\text{C}$			-1 -5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS} = 0\text{V}, V_{GS} = \pm 25\text{V}$			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$	-1.7	-2.3	-3	V
$I_{D(ON)}$	On state drain current	$V_{GS} = -10\text{V}, V_{DS} = -5\text{V}$	-80			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS} = -10\text{V}, I_D = -10\text{A}$		15	18	m Ω
		$T_J = 125^\circ\text{C}$		22	27	
		$V_{GS} = -5\text{V}, I_D = -5\text{A}$		27	36	
g_{FS}	Forward Transconductance	$V_{DS} = -5\text{V}, I_D = -10\text{A}$		22		S
V_{SD}	Diode Forward Voltage	$I_S = -1\text{A}, V_{GS} = 0\text{V}$		-0.74	-1	V
I_S	Maximum Body-Diode Continuous Current				-3.5	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}, V_{DS}=-15\text{V}, f=1\text{MHz}$		1130	1400	pF
C_{oss}	Output Capacitance		240		pF	
C_{rss}	Reverse Transfer Capacitance		155		pF	
R_g	Gate resistance	$V_{GS}=0\text{V}, V_{DS}=0\text{V}, f=1\text{MHz}$		5.8	8	Ω
SWITCHING PARAMETERS						
$Q_{g(10V)}$	Total Gate Charge	$V_{GS}=-10\text{V}, V_{DS}=-15\text{V}, I_D=-10\text{A}$		18	24	nC
$Q_{g(4.5V)}$	Total Gate Charge		9.5			
Q_{gs}	Gate Source Charge		5.5		nC	
Q_{gd}	Gate Drain Charge		3.3		nC	
$t_{D(on)}$	Turn-On Delay Time	$V_{GS}=-10\text{V}, V_{DS}=-15\text{V}, R_L=1.5\Omega,$ $R_{GEN}=3\Omega$		8.7		ns
t_r	Turn-On Rise Time		8.5		ns	
$t_{D(off)}$	Turn-Off Delay Time		18		ns	
t_f	Turn-Off Fall Time		7		ns	
t_{rr}	Body Diode Reverse Recovery Time	$I_F=-10\text{A}, di/dt=100\text{A}/\mu\text{s}$		25	30	ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=-10\text{A}, di/dt=100\text{A}/\mu\text{s}$		12		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$. The value in any given application depends on the user's specific board design. The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using $< 300 \mu\text{s}$ pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.

F: The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.

G: E_{AR} and I_{AR} ratings are based on low frequency and duty cycles to keep $T_J=25\text{C}$.

Rev0: Aug. 2007

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

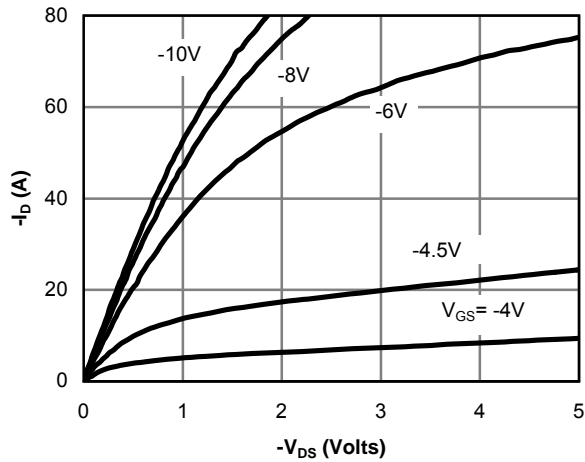


Figure 1: On-Region Characteristics

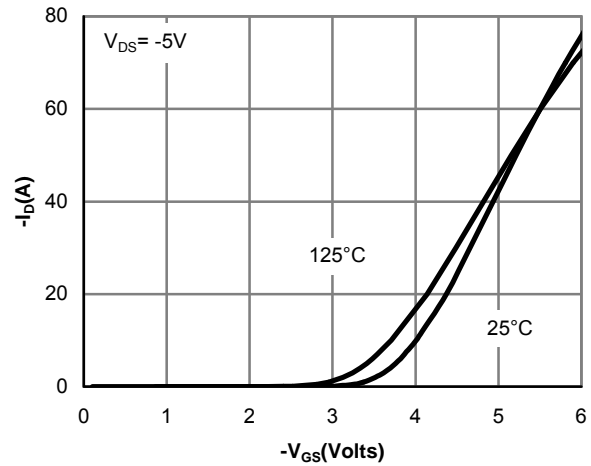


Figure 2: Transfer Characteristics

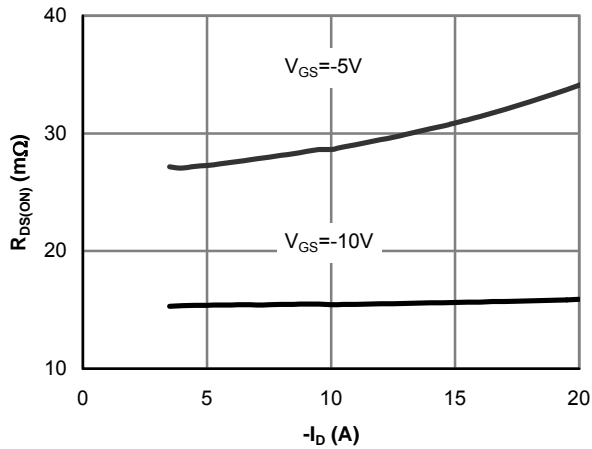


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

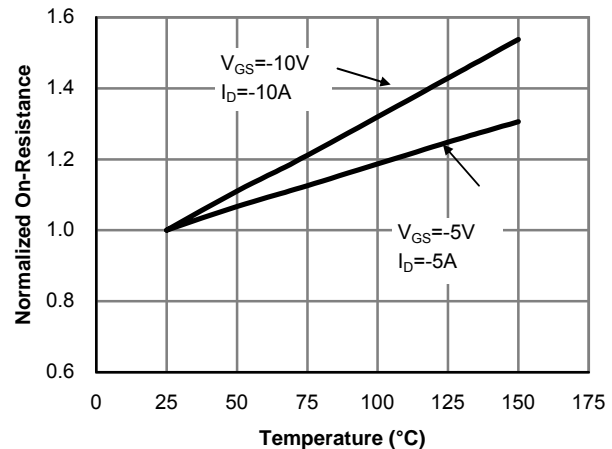


Figure 4: On-Resistance vs. Junction Temperature

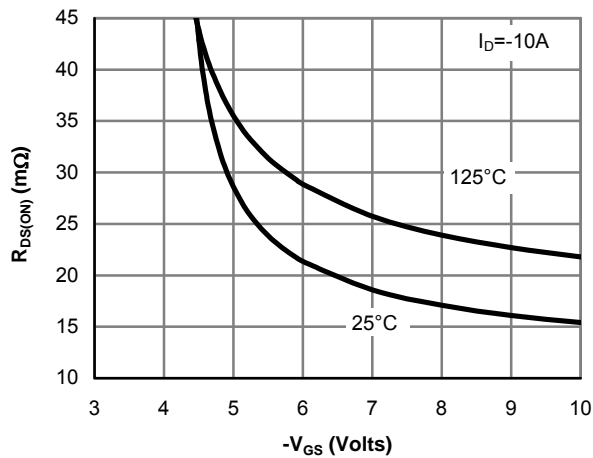


Figure 5: On-Resistance vs. Gate-Source Voltage

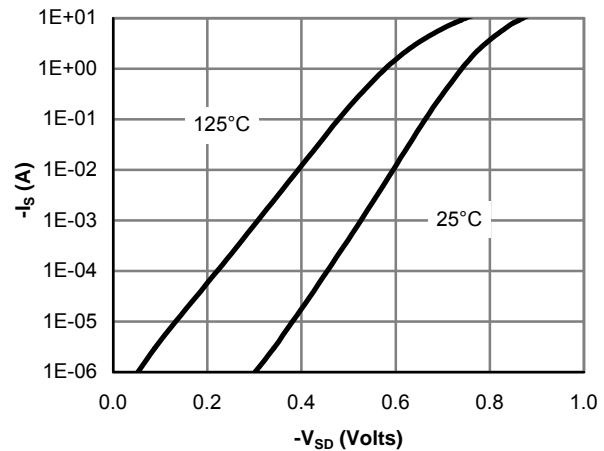


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

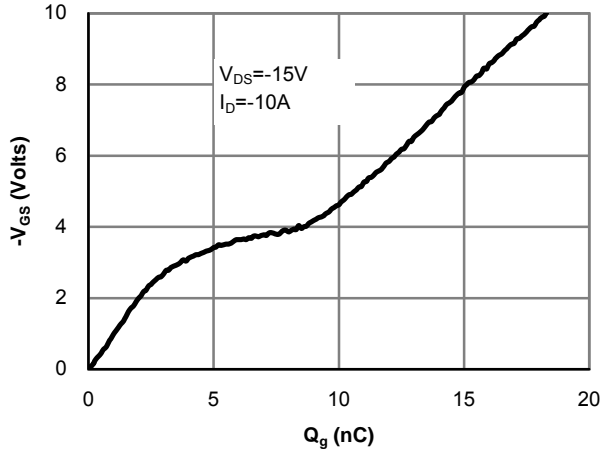


Figure 7: Gate-Charge Characteristics

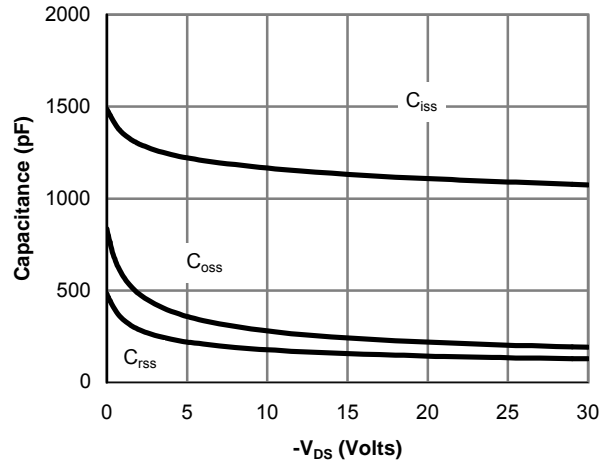


Figure 8: Capacitance Characteristics

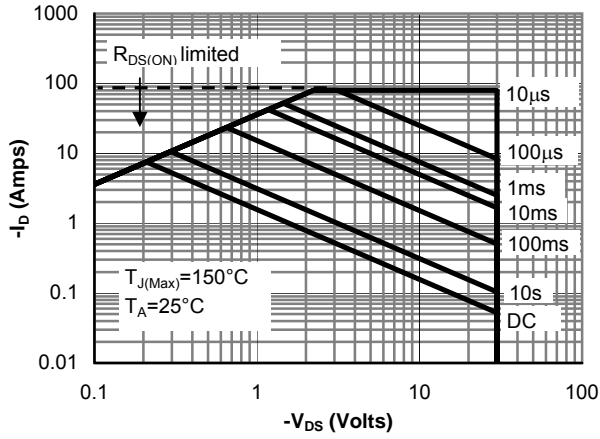


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

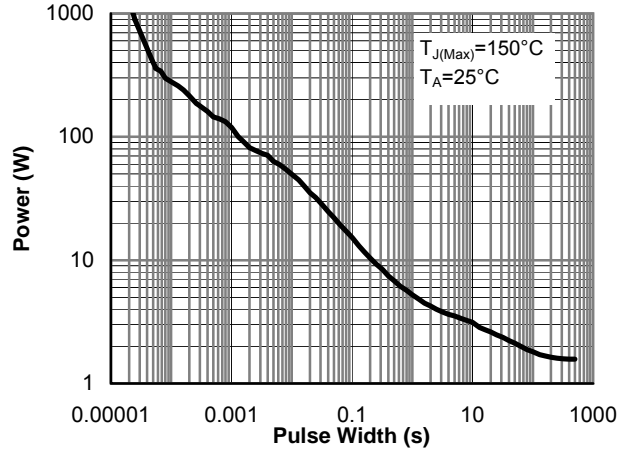


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

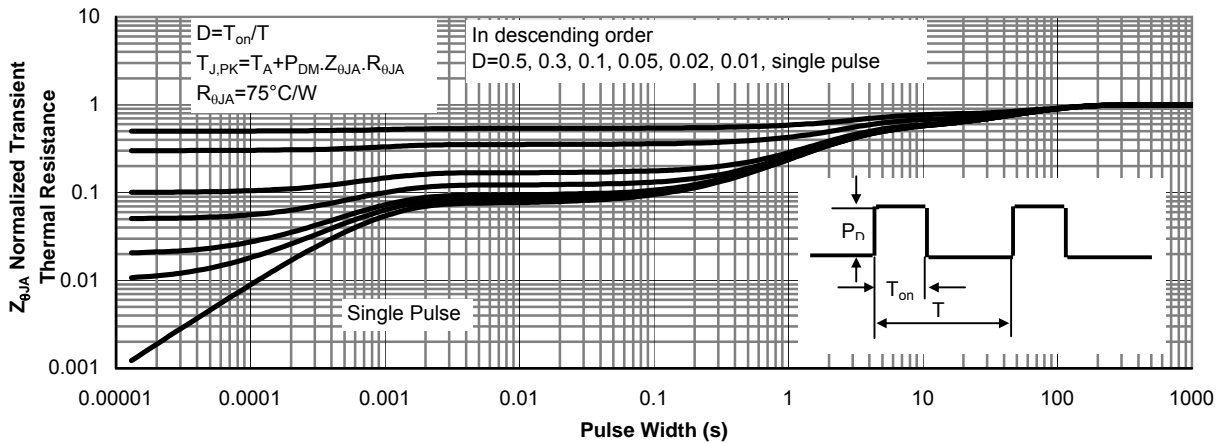


Figure 11: Normalized Maximum Transient Thermal Impedance (Note E)